Ordering number:EN2540A

PNP/NPN Epitaxial Planar Silicon Transistors

2SB1216/2SD1816

High-Current Switching Applications

Applications

· Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications.

Features

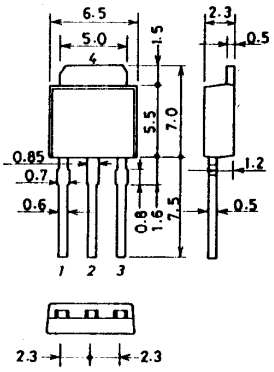
· Low collector-to-emitter saturation voltage.
· Good linearity of h_{FE}.
· Small and slim package facilitating compactness of sets.
· High f_T.
· Fast switching time.

Package Dimensions

unit:mm

2045B

[2SB1216/2SD1816]



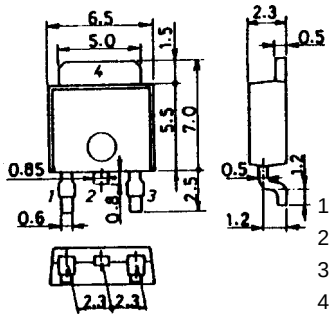
1 : Base
2 : Collector
3 : Emitter
4 : Collector

SANYO : TP

unit:mm

2044B

[2SB1216/2SD1816]



1 : Base
2 : Collector
3 : Emitter
4 : Collector

SANYO : TP-FA

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

( ) : 2SB1216

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(–)120	V
Collector-to-Emitter Voltage	V_{CEO}		(–)100	V
Emitter-to-Base Voltage	V_{EBO}		(–)6	V
Collector Current	I_C		(–)4	A
Collector Current (Pulse)	I_{CP}		(–)8	A
Collector Dissipation	P_C		1	W
		Tc=25˚C	20	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

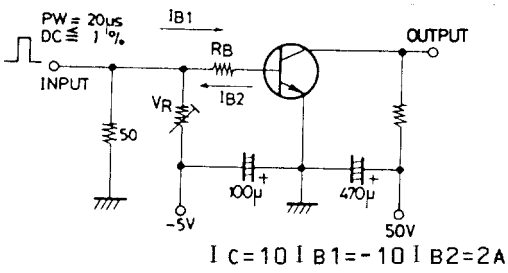
Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(–)100V, I_E=0			(–)1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(–)4V, I_C=0			(–)1	µA
DC Current Gain	$h_{FE}1$	V_{CE}=(–)5V, I_C=(–)0.5A	70*		400*	
	$h_{FE}2$	V_{CE}=(–)5V, I_C=(–)3A	40			
Gain-Bandwidth Product	f_T	V_{CE}=(–)10V, I_C=(–)0.5A		(130)		MHz
				180		MHz
Output Capacitance	C_{ob}	V_{CB}=(–)10V, f=1MHz		(65)40		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=(–)2A, I_B=(–)0.2A		150	400	mV
				(–200)	(–500)	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=(–)2A, I_B=(–)0.2A		(–)0.9	(–)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(–)10µA, I_E=0	(–)120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(–)1mA, R_{BE}=∞	(–)100			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(–)10µA, I_C=0	(–)6			V
Turn-ON Time	t_{on}	See specified Test Circuit		100		ns
Storage Time	t_{stg}	See specified Test Circuit		(800)		ns
				900		ns
Fall Time	t_f	See specified Test Circuit		50		ns

* : The 2SB1216/2SD1816 are classified by 0.5A h_{FE} as follows :

70	Q	140	100	R	200	140	S	280	200	T	400

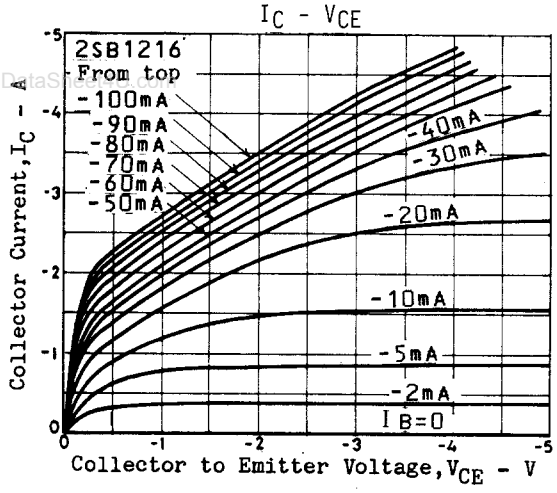
Switching Time Test Circuit

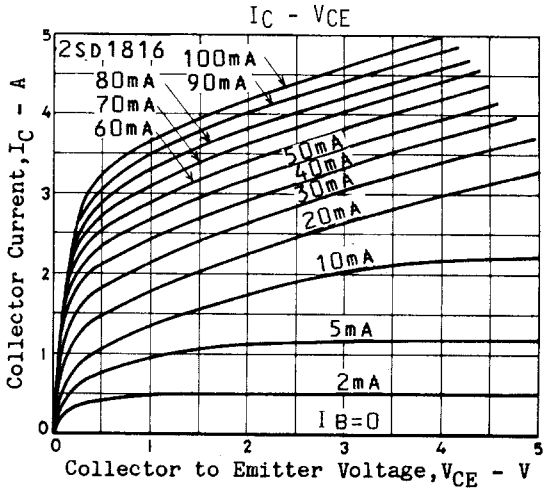


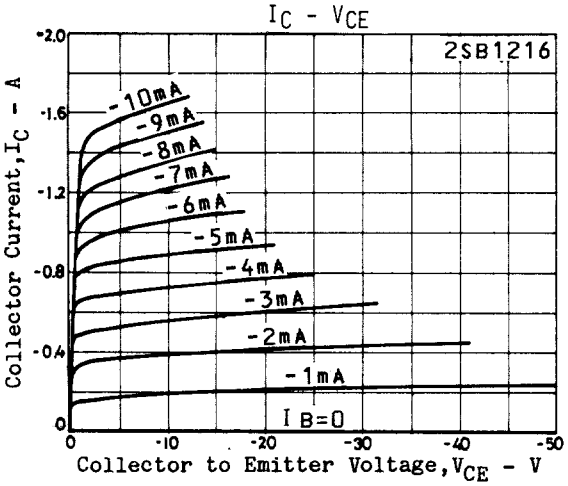
$I_C = 10 I_{B1} = -10 I_{B2} = 2A$

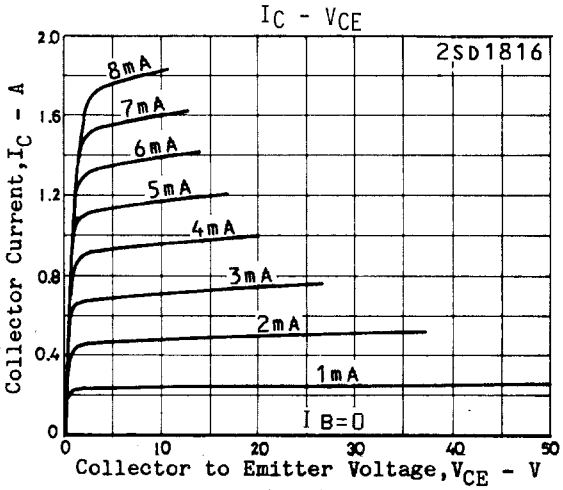
(For PNP, minus sign is omitted.)

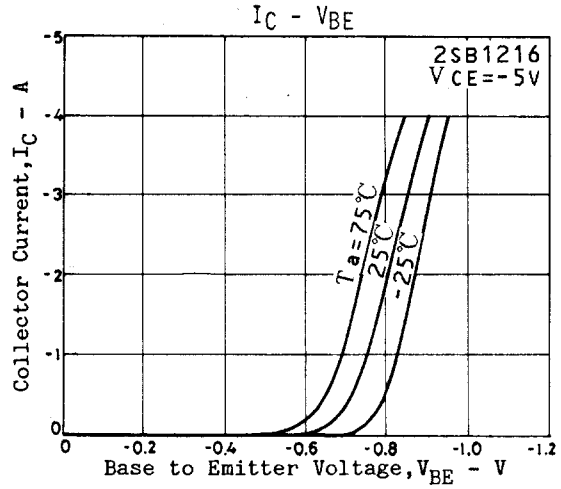
Unit (resistance : Ω, capacitance : F)

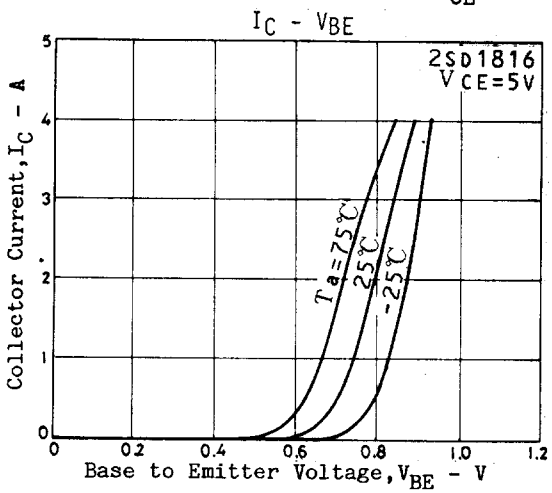


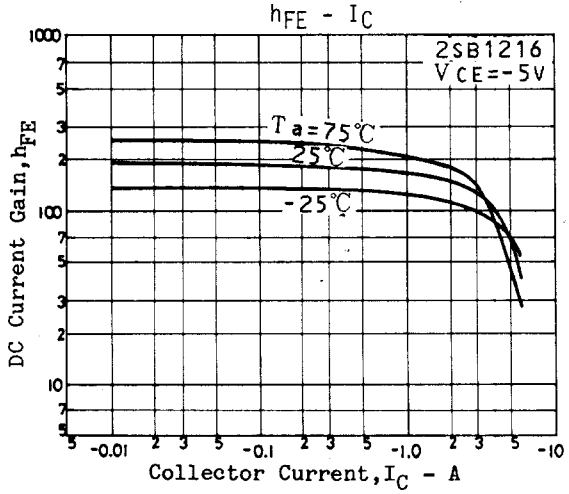


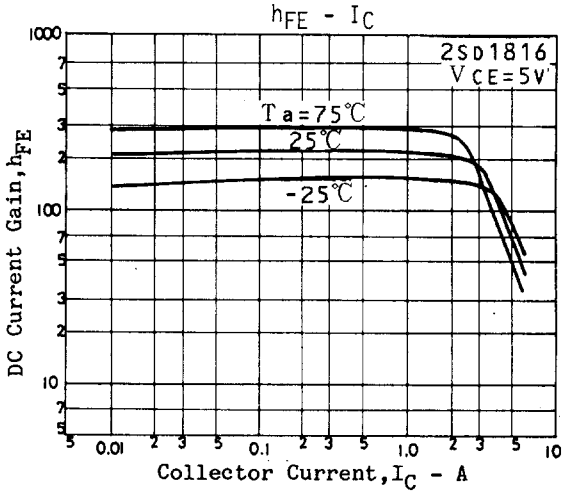




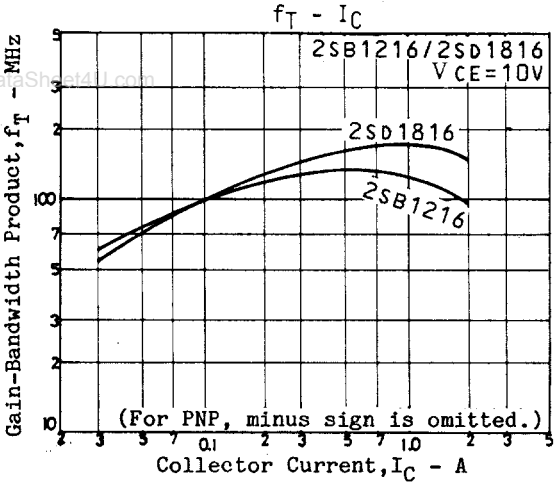




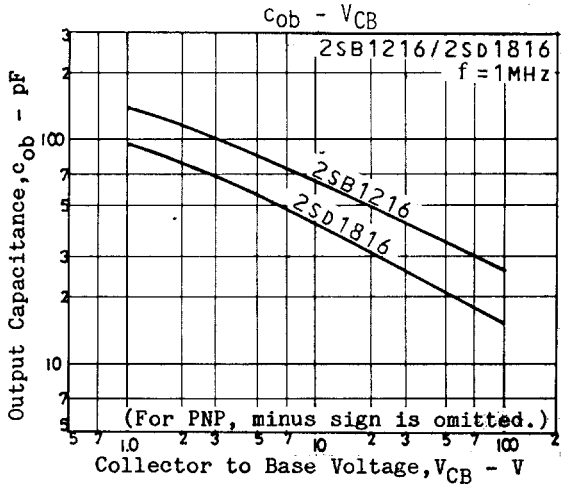




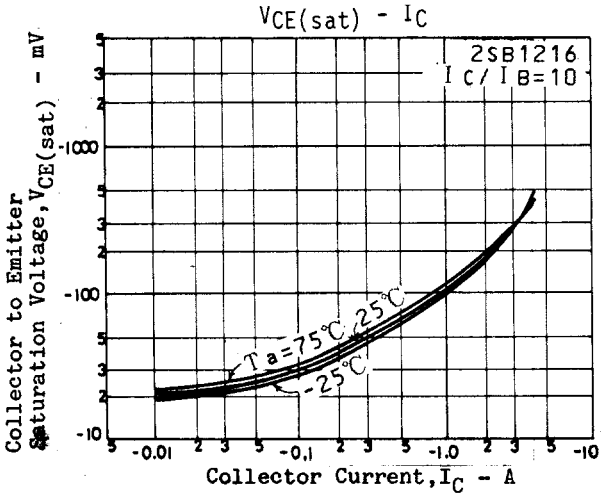
f_T - I_C



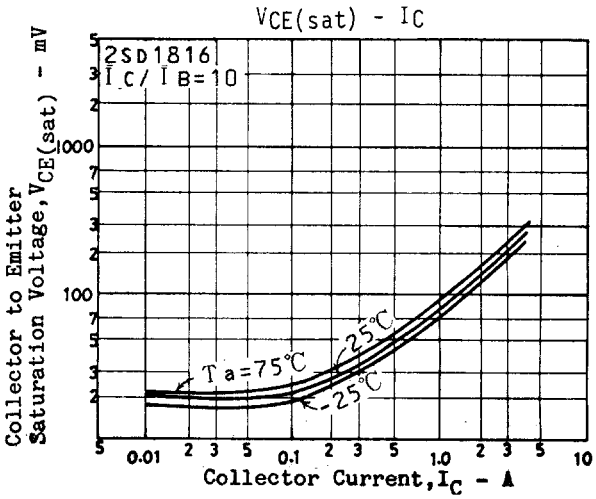
C_{ob} - V_{CB}



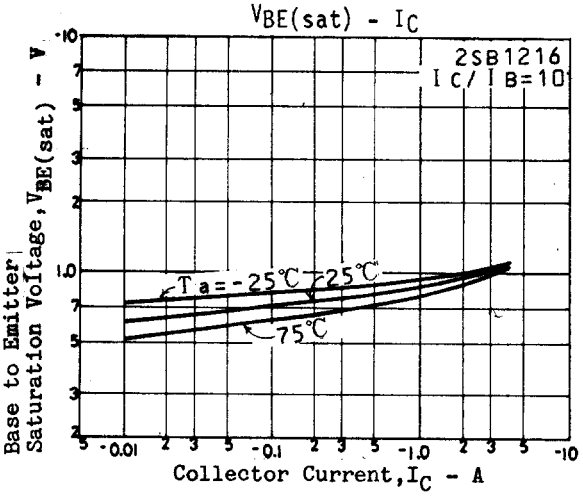
$V_{CE(sat)}$ - I_C



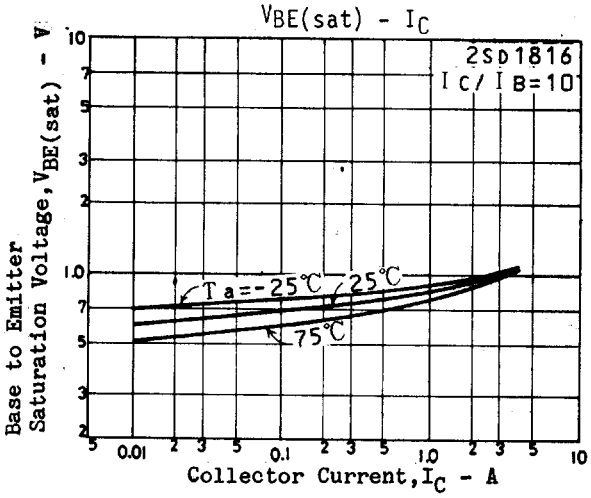
$V_{CE(sat)}$ - I_C



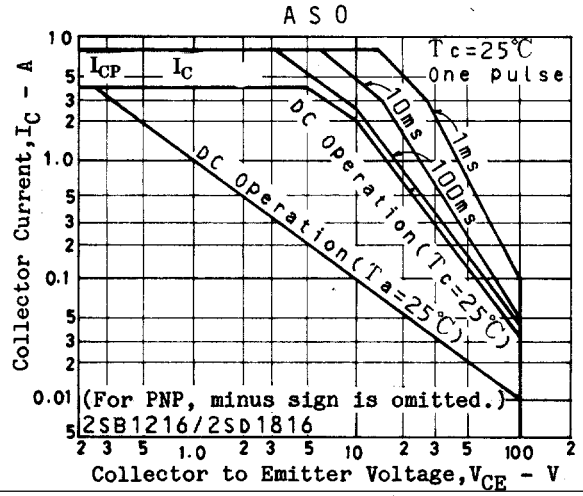
$V_{BE(sat)}$ - I_C



$V_{BE(sat)}$ - I_C



A S O



P_C - T_a